

Title (en)

GATE STRUCTURE AND METHOD FOR MAKING SAME

Title (de)

GATESTRUKTUR UND HERSTELLUNGSVERFAHREN DAFÜR

Title (fr)

STRUCTURE DE GRILLE ET PROCEDE DE FABRICATION

Publication

EP 1831929 A1 20070912 (FR)

Application

EP 05810641 A 20051005

Priority

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- FR 0452272 A 20041005

Abstract (en)

[origin: WO2006037927A1] The invention concerns a MOS transistor whereof the gate comprises successively an insulating layer (31), a metal silicide layer (50), an encapsulating conductive material layer (53), and a polysilicon layer (55).

IPC 8 full level

H01L 29/49 (2006.01); **H01L 21/8238** (2006.01)

CPC (source: EP US)

H01L 21/28026 (2013.01 - EP US); **H01L 29/665** (2013.01 - EP US)

Citation (search report)

See references of WO 2006037927A1

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